



### 60V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> MAX	I <sub>D MAX</sub> T <sub>C</sub> = +25°C
60V	$16.5 \text{m}\Omega$ @ $V_{GS} = 10 \text{V}$	43A
	$26m\Omega @ V_{GS} = 4.5V$	34A

#### **Features**

- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

### **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

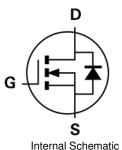
- Synchronous Rectifier
- Backlighting
- Power Management Functions
- DC-DC Converters

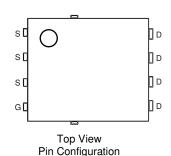
### **Mechanical Data**

- Case: PowerDI<sup>®</sup> 5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe;
   Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)

#### PowerDI5060-8 (SWP) (Type UX)







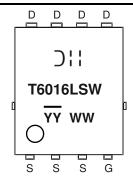
### Ordering Information (Note 4)

Part Number	Case	Packaging	
DMT6016LPSW-13	PowerDI5060-8 (SWP) (Type UX)	2,500 / Tape & Reel	

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



Oll = Manufacturer's Marking
T6016LSW = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 19 = 2019)
WW = Week Code (01 to 53)



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V <sub>DSS</sub>	60	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 5)	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	11.2 9.0	Α
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 6)	$T_C = +25$ °C $T_C = +70$ °C	I <sub>D</sub>	43.0 34.4	Α
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	170	Α	
Maximum Continuous Body Diode Forward Current (Note 6)	Is	40	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle	I <sub>SM</sub>	170	Α	
Avalanche Current, L=0.1mH		I <sub>AS</sub>	15.3	Α
Avalanche Energy, L=0.1mH		E <sub>AS</sub>	11.7	mJ

### **Thermal Characteristics**

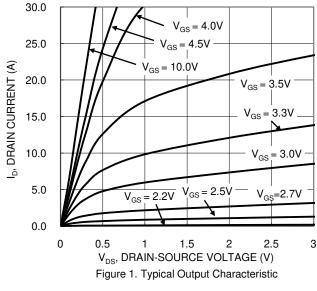
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25$ °C	$P_{D}$	2.84	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	44	°C/W	
Total Power Dissipation (Note 6) $T_C = +25^{\circ}C$		$P_{D}$	41.67	W
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	3	°C/W
Operating and Storage Temperature Range		$T_{J_1}T_{STG}$	-55 to +150	°C

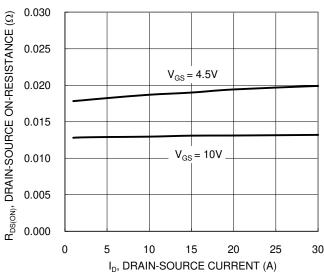
### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

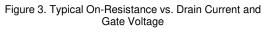
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)			. , , , ,		•		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	-	-	1	μA	V <sub>DS</sub> = 48V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	-	2.5	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	Б	-	13	16.5	m0	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	-	19	26	mΩ	$V_{GS} = 4.5V, I_D = 18A$	
Diode Forward Voltage	V <sub>SD</sub>	-	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A	
DYNAMIC CHARACTERISTICS (Note 8)				•		•	
Input Capacitance	C <sub>iss</sub>	-	864	-		$V_{DS} = 30V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Output Capacitance	Coss	-	282	-	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	1	27	-			
Gate Resistance	$R_g$	-	1.3	-	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	-	8.4	-			
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	-	17	-	nC	V 20V I 10A	
Gate-Source Charge	$Q_{gs}$	-	3.1	-	110	$V_{DS} = 30V, I_{D} = 10A$	
Gate-Drain Charge	$Q_{gd}$	-	4.3	-			
Turn-On Delay Time	t <sub>D(ON)</sub>	-	3.4	-			
Turn-On Rise Time	t <sub>R</sub>	-	5.2	-	20	$V_{DS} = 30V, V_{GS} = 10V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	13	-	ns	$I_D = 10A$ , $R_q = 6\Omega$	
Turn-Off Fall Time	t <sub>F</sub>	-	7	-			
Body Diode Reverse Recovery Time	t <sub>RR</sub>	-	22	-	ns	I_ 10.0 di/dt 1000/up	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	-	11	-	nC	$I_F = 10A$ , di/dt = 100A/ $\mu$ s	

 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad).
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing. Notes:









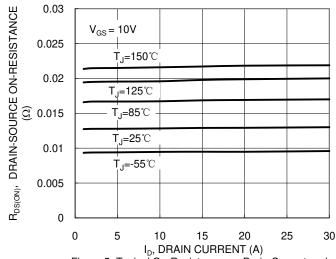


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

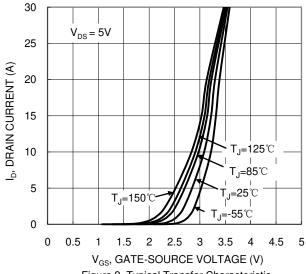


Figure 2. Typical Transfer Characteristic

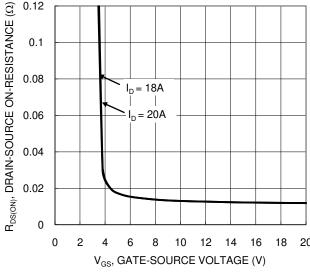


Figure 4. Typical Transfer Characteristic

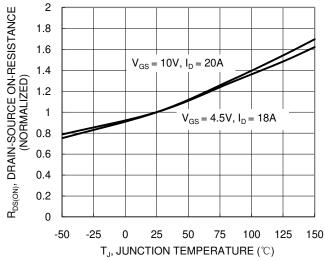


Figure 6. On-Resistance Variation with Temperature



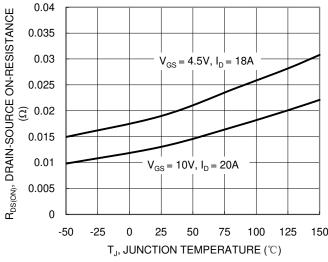
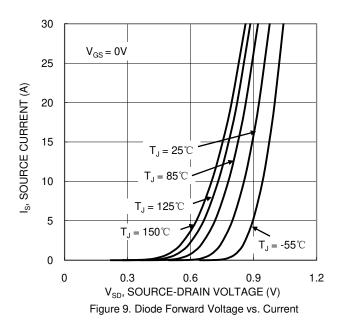


Figure 7. On-Resistance Variation with Temperature



10 8 6  $V_{GS}(V)$ 4  $V_{DS} = 30V, I_{D} = 10A$ 2 0 0 2 10 12 14 16 18 Qg (nC) Figure 11. Gate Charge

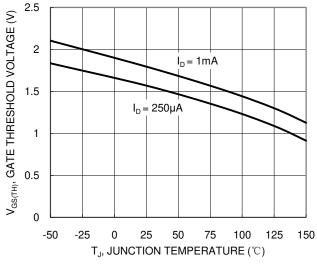


Figure 8. Gate Threshold Variation vs. Junction Temperature

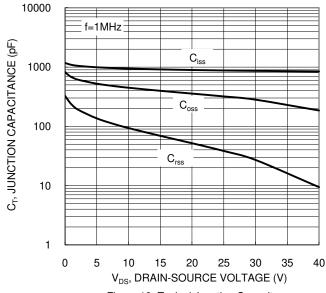
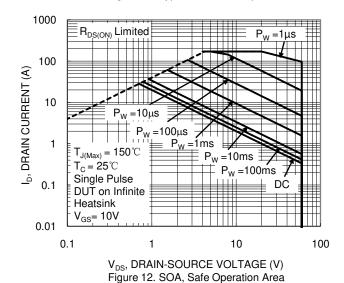


Figure 10. Typical Junction Capacitance





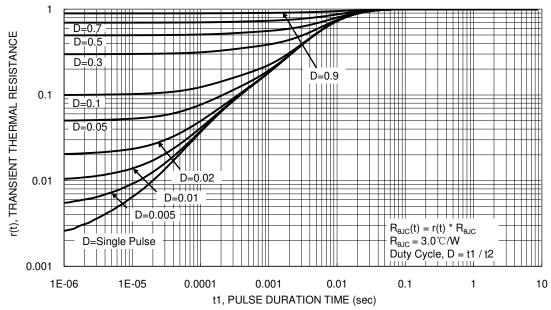


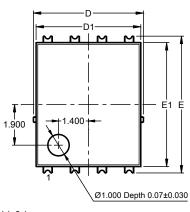
Figure 13. Transient Thermal Resistance

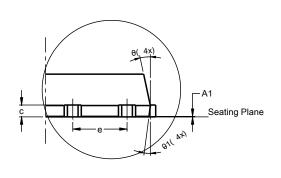


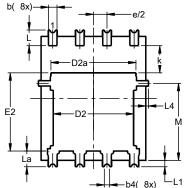
## **Package Outline Dimensions**

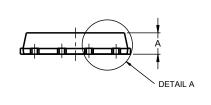
Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (SWP) (Type UX)









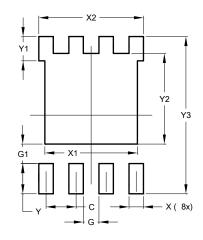
DETAIL A

PowerDI5060-8 (SWP)						
(Type UX) ´						
Dim	Min	Max	Тур			
Α	0.90	1.10	1.00			
<b>A</b> 1	0	0.05				
b	0.30	0.50	0.41			
b2	0.20	0.35	0.25			
b4	(	).25REF	=			
С	0.230	0.330	0.277			
D	5	.15 BS0	$\sim$			
D1	4.70	5.10	4.90			
D2	3.56	3.96	3.76			
D2a	3.78	3.98				
Е	6	.40 BS0	$\sim$			
E1	5.60	6.00	5.80			
E2	3.46	3.86	3.66			
E2a	4.195	4.595	4.395			
е	1.27BSC					
k	1.05					
L	0.635	0.835	0.735			
La	0.635	0.835	0.735			
L1	0.200	0.400	0.300			
L1a	0.050REF					
L4	0.025	0.225	0.125			
М	3.205	4.005	3.605			
θ	10°	12°	11°			
θ1	6°	8°	7°			
All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (SWP) (Type UX)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	4.100		
X2	4.420		
Υ	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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